SHD626010 SHD626010D SHD626010N SHD626010P

**TECHNICAL DATA** DATA SHEET 4076, REV. E

# HERMETIC SILICON CARBIDE RECTIFIER

#### **DESCRIPTION/FEATURES:**

A 300-VOLT, 40 AMP, POWER SILICON CARBIDE RECTIFIER IN A HERMETIC TO-257 PACKAGE AVAILABLE SCREENED TO ANY REQUIRED LEVEL

- NO RECOVERY TIME OR REVERSE RECOVERY LOSSES
- NO TEMPERATURE INFLUENCE ON SWITCHING BEHAVIOR
- **High Temperature Option** Maximum operation & storage temperature can be increased to 250°C; use part number prefix as SHDT
- High Frequency Option Non-magnetic Glidcop leads are available for improved performance at high frequency; use part number prefix SHDG
- Ceramic Seal Option For ceramic seals use part number prefix SHDC

### **MAXIMUM RATINGS**

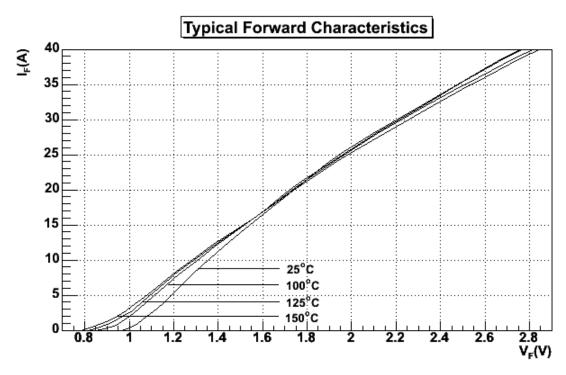
ALL RATINGS ARE @  $T_C$  = 25 °C UNLESS OTHERWISE SPECIFIED.

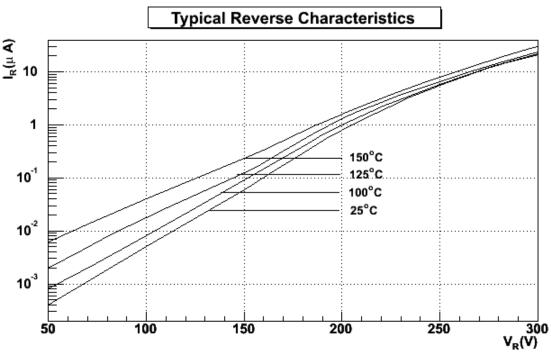
RATING	SYMBOL	MAX.	UNIT S
PEAK INVERSE VOLTAGE	PIV	300	Volts
MAXIMUM DC OUTPUT CURRENT (With $T_C = 65$ $^{\circ}$ C, for part numbers with P and N suffixes)	lo	40	Amps
MAXIMUM DC OUTPUT CURRENT (With $T_C = 65$ $^{\rm O}$ C, for part numbers with Single and D suffixes)	lo	20	Amps
MAXIMUM REPETITIVE FORWARD SURGE CURRENT PER LEG (t = 8.3ms, Sine) per leg, $T_C$ = 25 $^{\circ}$ C	I <sub>FRM</sub>	45	Amps
MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT PER LEG (t = 10 $\mu$ s, Pulse) per leg, T <sub>C</sub> = 25 $^{\circ}$ C	I <sub>FSM</sub>	100	Amps
MAXIMUM JUNCTION CAPACITANCE (V <sub>r</sub> =5V) per leg	Ст	450	pF
MAXIMUM POWER DISSIPATION, T <sub>C</sub> = 25 °C	P <sub>d</sub>	65	W
MAXIMUM THERMAL RESISTANCE, Junction to Case (PER DUAL PACKAGE For Common Cathode/Anode Configurations)	R <sub>e</sub> JC	2.5	°C/W
MAXIMUM OPERATING AND STORAGE TEMPERATURE RANGE	Top, Tstg	-55 to +175	°C

## **ELECTRICAL CHARACTERISTICS**

CHARACTERISTIC		TYP	MAX.	UNIT S
MAXIMUM FORWARD VOLTAGE DROP, Pulsed	T <sub>J</sub> = 25 °C	1.35	1.50	
$(I_f = 10 \text{ A PER LEG}) V_f$	T <sub>J</sub> =150°C	1.30	1.45	Volts
MAXIMUM FORWARD VOLTAGE DROP, Pulsed	T <sub>J</sub> = 25 °C	1.70	1.90	
$(I_f = 20 \text{ A PER LEG}) V_f$	T <sub>J</sub> = 150 °C	1.75	2.00	Volts
MAXIMUM REVERSE CURRENT (Ir @ 300V PIV PER	LEG) T <sub>J</sub> = 25 °C	0.04	0.40	mA
	T <sub>J</sub> = 150 °C	0.12	2.00	
TOTAL CAPACITIVE CHARGE ( $V_R$ =200V $I_F$ =20A di/dt=200A/ $\mu$ s $T_J$ =25°C) $Q_C$ per leg		26	N/A	nC

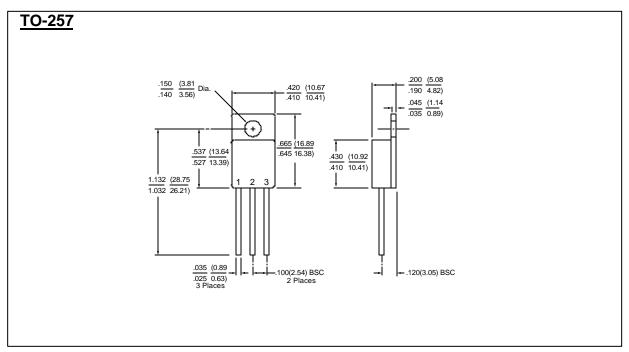
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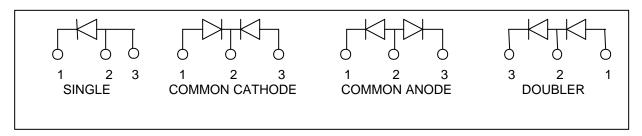
### **MECHANICAL DIMENSIONS**



## **PINOUT TABLE**

TYPE	PIN 1	PIN 2	PIN 3
SINGLE RECTIFIER	CATHODE	ANODE	ANODE
DUAL RECTIFIER/COMMON CATHODE (P)	ANODE 1	COMMON CATHODE	ANODE 2
DUAL RECTIFIER/COMMON ANODE (N)	CATHODE 1	COMMON ANODE	CATHODE 2
DUAL RECTIFIER/DOUBLER (D)	ANODE	ANODE/ CATHODE	CATHODE

### **SCHEMATIC**



Application Note: Customers should be aware that at the current stage of technical development of SiC, the reverse avalanche capabilities of the device are limited.

Customer designs will need to accommodate these limitations and avoid exposure of the device to this and other potentially damaging conditions in their applications.



#### **TECHNICAL DATA**

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